



Fast Recovery Diodes (Hockey PUK Version), 1650/1825 A



DO-200AC (K-PUK)

FEATURES

- High power FAST recovery diode series
- 2.0 μ s to 3.0 μ s recovery time
- High voltage ratings up to 3000 V
- High current capability
- Optimized turn-on and turn-off characteristics
- Low forward recovery
- Fast and soft reverse recovery
- Press PUK encapsulation
- Case style conform to JEDEC® DO-200AC (K-PUK)
- Maximum junction temperature 150 °C
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT

PRODUCT SUMMARY	
$I_{F(AV)}$	1650/1825 A
Package	DO-200AC (K-PUK)
Circuit configuration	Single diode

TYPICAL APPLICATIONS

- Snubber diode for GTO
- High voltage freewheeling diode
- Fast recovery rectifier applications

MAJOR RATINGS AND CHARACTERISTICS				
PARAMETER	TEST CONDITIONS	SD1553C..K		UNITS
		S20	S30	
$I_{F(AV)}$		1825	1650	A
	T_{hs}	55	55	°C
$I_{F(RMS)}$		3100	2800	A
I_{FSM}	50 Hz	25 000	22 000	
	60 Hz	26 180	23 000	
V_{RRM}	Range	1800 to 2500	1800 to 3000	V
t_{rr}		2.0	3.0	μ s
	T_J	25		°C
T_J	-40 to 150			

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS				
TYPE NUMBER	VOLTAGE CODE	V_{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
VS-SD1553C..S20K	18	1800	1900	75
	22	2200	2300	
	25	2500	2600	
VS-SD1553C..S30K	18	1800	1900	
	22	2200	2300	
	25	2500	2600	
	28	2800	2900	
	30	3000	3100	



FORWARD CONDUCTION							
PARAMETER	SYMBOL	TEST CONDITIONS		SD1553C..K		UNITS	
				S20	S30		
Maximum average forward current at heatsink temperature	$I_{F(AV)}$	180° conduction, half sine wave Double side (single side) cooled		1825 (865)	1650 (790)	A	
Maximum RMS forward current	$I_{F(RMS)}$	25 °C heatsink temperature double side cooled		3100	2800	°C	
Maximum peak, one-cycle forward, non-repetitive surge current	I_{FSM}	t = 10 ms	No voltage reappplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	25 000	22 000	A
		t = 8.3 ms			26 180	23 000	
		t = 10 ms	100 % V_{RRM} reappplied		21 030	18 500	
		t = 8.3 ms			22 010	19 370	
Maximum I^2t for fusing	I^2t	t = 10 ms	No voltage reappplied		3126	2421	kA ² s
		t = 8.3 ms			2854	2210	
		t = 10 ms	100 % V_{RRM} reappplied		2210	1712	
		t = 8.3 ms			2018	1563	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 to 10 ms, no voltage reappplied		31 260	24 210	kA ² √s	
Low level value of threshold voltage	$V_{F(TO)1}$	$(16.7 \% \times \pi \times I_{F(AV)} < I < \pi \times I_{F(AV)})$, $T_J = T_J$ maximum		1.15	1.31	V	
High level value of threshold voltage	$V_{F(TO)2}$	$(I > \pi \times I_{F(AV)})$, $T_J = T_J$ maximum		1.29	1.45		
Low level value of forward slope resistance	r_{f1}	$(16.7 \% \times \pi \times I_{F(AV)} < I < \pi \times I_{F(AV)})$, $T_J = T_J$ maximum		0.27	0.32	mW	
High level value of forward slope resistance	r_{f2}	$(I > \pi \times I_{F(AV)})$, $T_J = T_J$ maximum		0.25	0.30		
Maximum forward voltage drop	V_{FM}	$I_{pk} = 4000$ A, $T_J = T_J$ maximum, $t_p = 10$ ms sinusoidal wave		2.23	2.60	V	

RECOVERY CHARACTERISTICS								
CODE	MAXIMUM VALUE AT $T_J = 25$ °C		TEST CONDITIONS			TYPICAL VALUES AT $T_J = 150$ °C		
	t_{rr} AT 25 % I_{RRM} (μs)	I_{pk} SQUARE PULSE (A)	di/dt (A/μs)	V_r (V)	t_{rr} AT 25 % I_{RRM} (μs)	Q_{rr} (μC)	I_{rr} (A)	
S20	2.0	1000	100	- 50	4.5	650	240	
S30	3.0				5.0	780	260	

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction operating and storage temperature range	T_J, T_{Stg}		-40 to 150	°C
Maximum thermal resistance, case junction to heatsink	R_{thJ-hs}	DC operation single side cooled	0.04	K/W
		DC operation double side cooled	0.02	
Mounting force, ± 10 %			22 250 (2250)	N (kg)
Approximate weight			425	g
Case style		See dimensions - link at the end of datasheet	DO-200AC (K-PUK)	

ΔR_{thJ-hs} CONDUCTION						
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEST CONDITIONS	UNITS
	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE		
180°	0.0018	0.0019	0.0012	0.0012	$T_J = T_J$ maximum	K/W
120°	0.0021	0.0021	0.0021	0.0021		
90°	0.0027	0.0027	0.0029	0.0029		
60°	0.0039	0.0039	0.0041	0.0041		
30°	0.0067	0.0067	0.0068	0.0068		

Note

- The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC

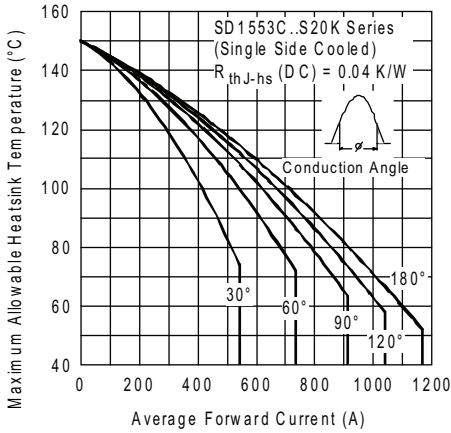


Fig. 1 - Current Ratings Characteristics

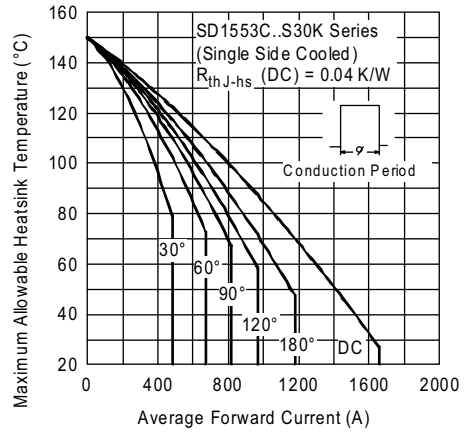


Fig. 4 - Current Ratings Characteristics

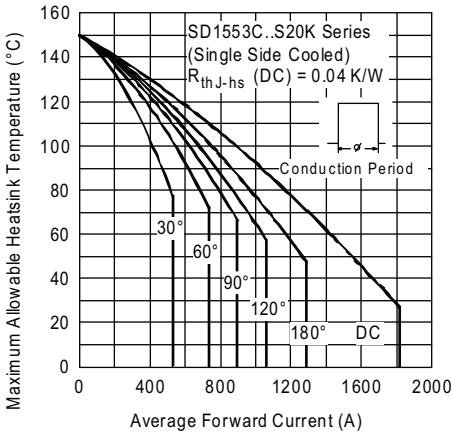


Fig. 2 - Current Ratings Characteristics

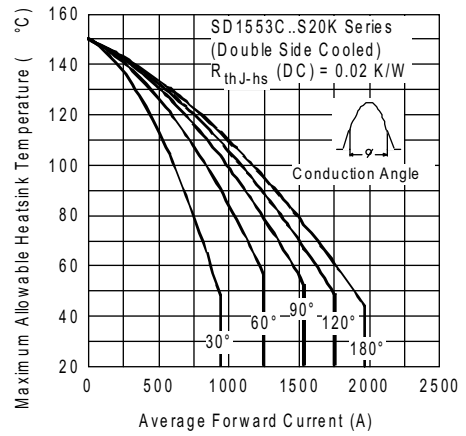


Fig. 5 - Current Ratings Characteristics

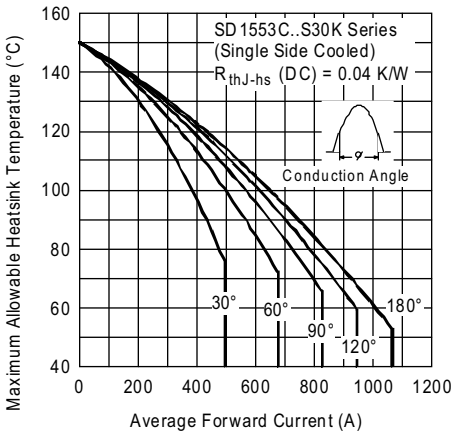


Fig. 3 - Current Ratings Characteristics

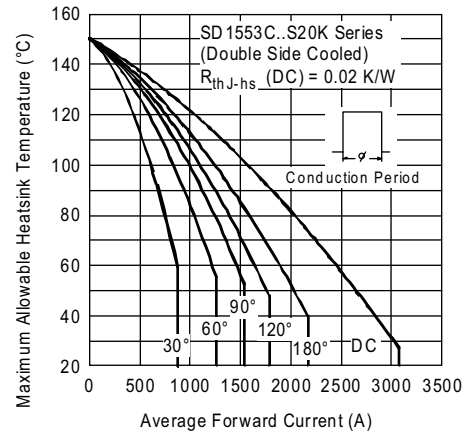


Fig. 6 - Current Ratings Characteristics

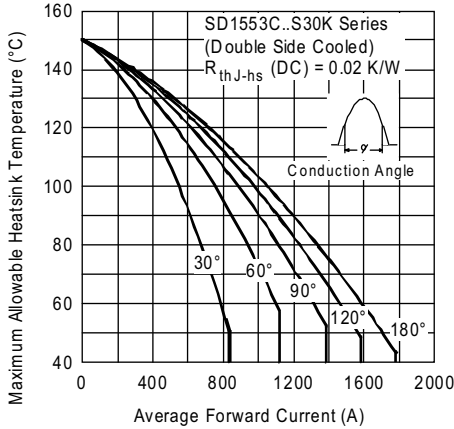


Fig. 7 - Current Ratings Characteristics

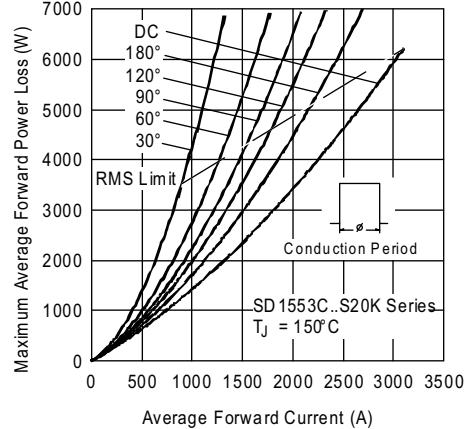


Fig. 10 - Forward Power Loss Characteristics

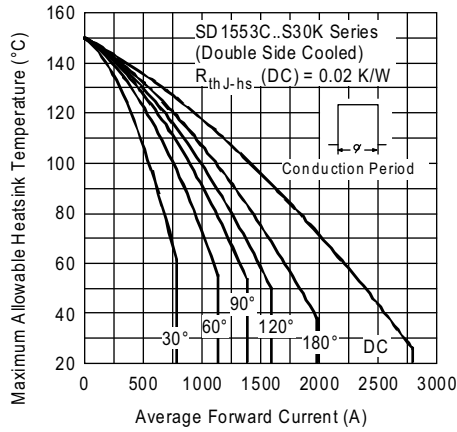


Fig. 8 - Current Ratings Characteristics

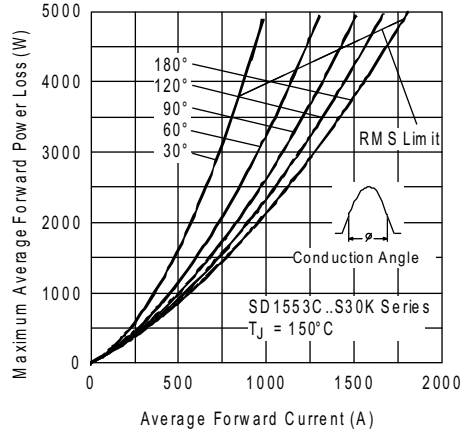


Fig. 11 - Forward Power Loss Characteristics

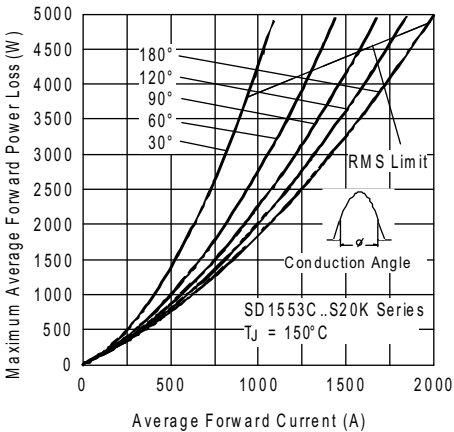


Fig. 9 - Forward Power Loss Characteristics

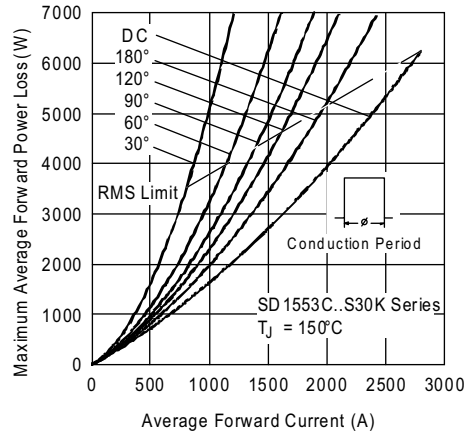


Fig. 12 - Forward Power Loss Characteristics

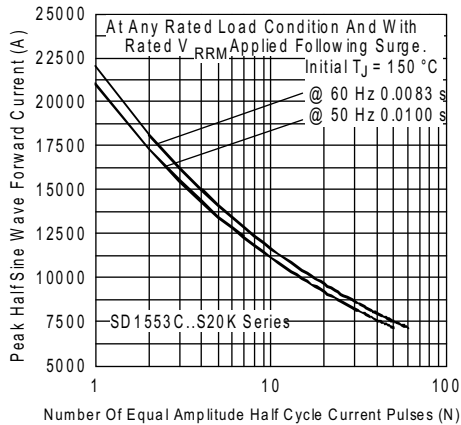


Fig. 13 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

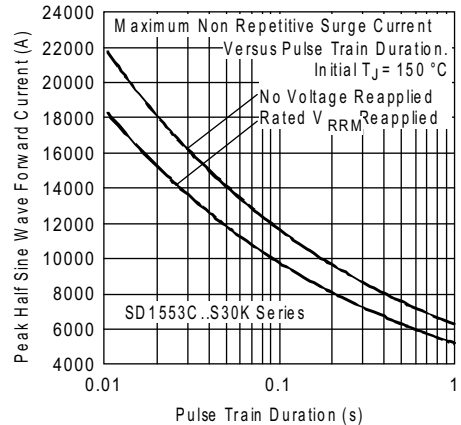


Fig. 16 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

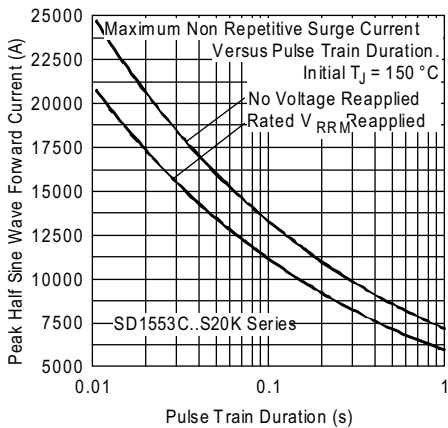


Fig. 14 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

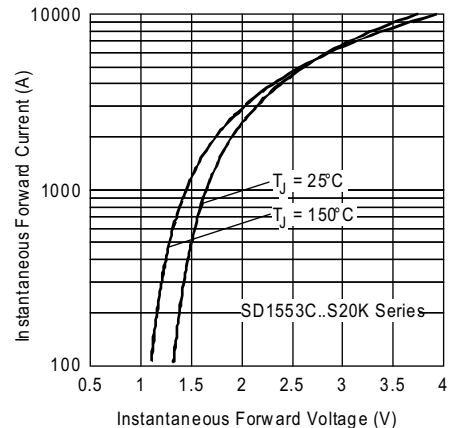


Fig. 17 - Forward Voltage Drop Characteristics

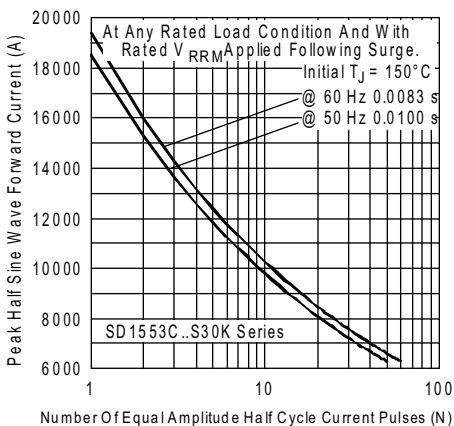


Fig. 15 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

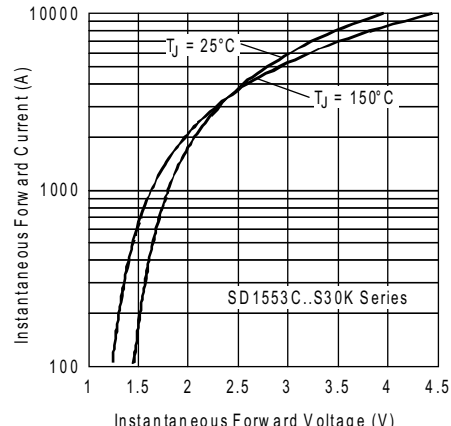


Fig. 18 - Forward Voltage Drop Characteristics

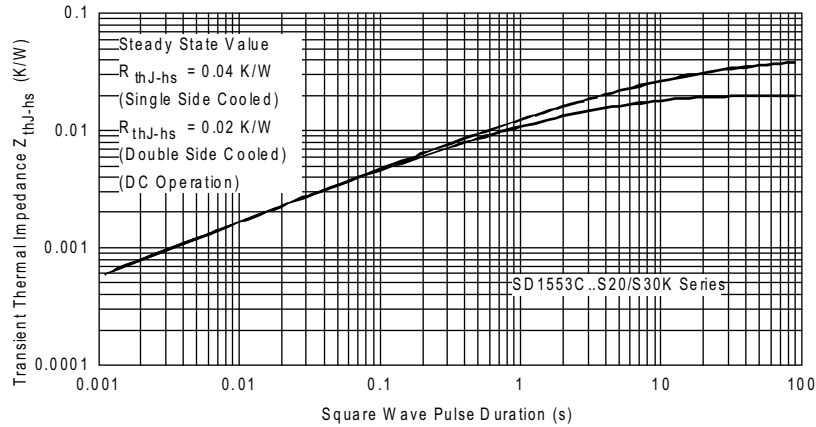


Fig. 19 - Thermal Impedance Z_{thJ-hs} Characteristic

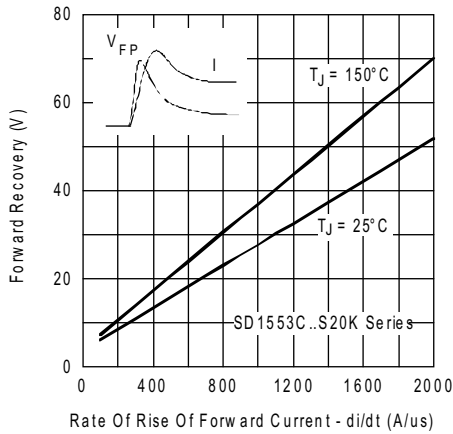


Fig. 20 - Typical Forward Recovery Characteristics

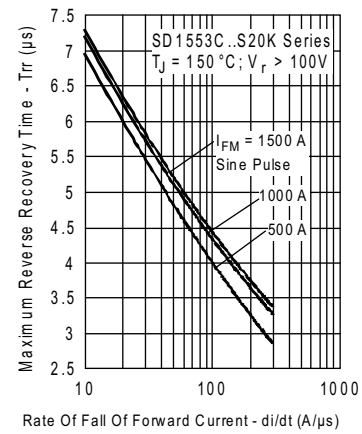


Fig. 22 - Recovery Time Characteristics

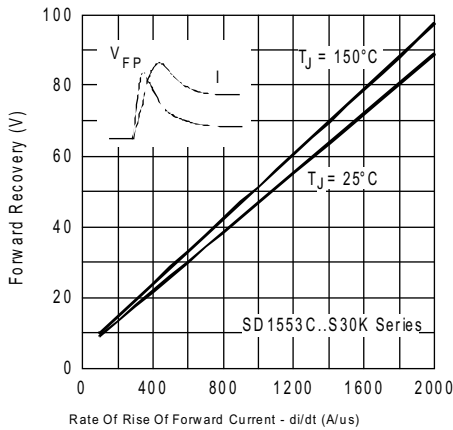


Fig. 21 - Typical Forward Recovery Characteristics

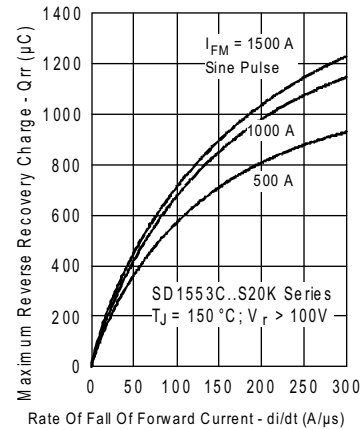


Fig. 23 - Recovery Charge Characteristics

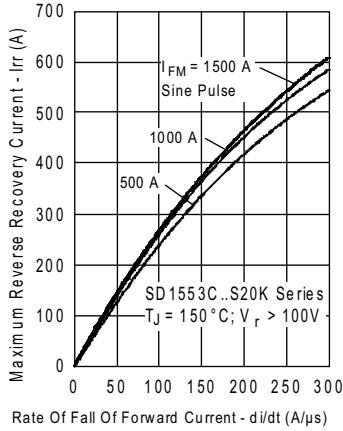


Fig. 24 - Recovery Current Characteristics

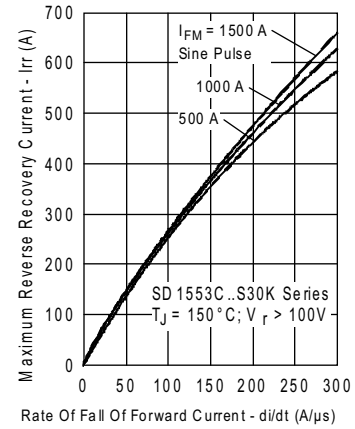


Fig. 27 - Recovery Current Characteristics

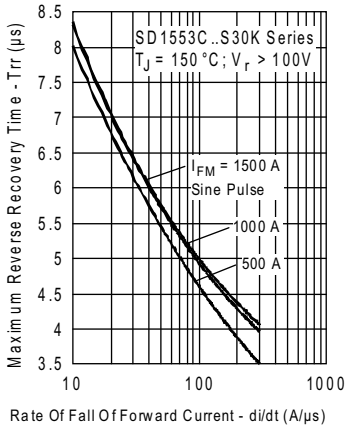


Fig. 25 - Recovery Time Characteristics

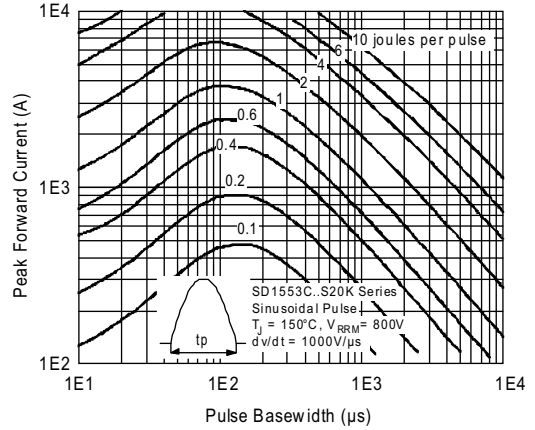


Fig. 28 - Maximum Total Energy Loss Per Pulse Characteristics

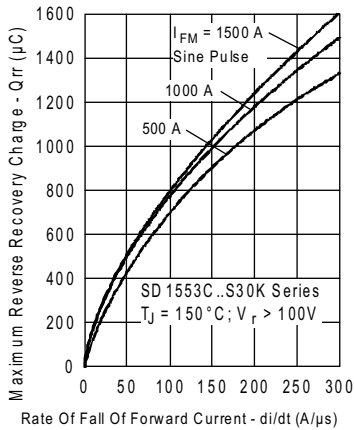


Fig. 26 - Recovery Charge Characteristics

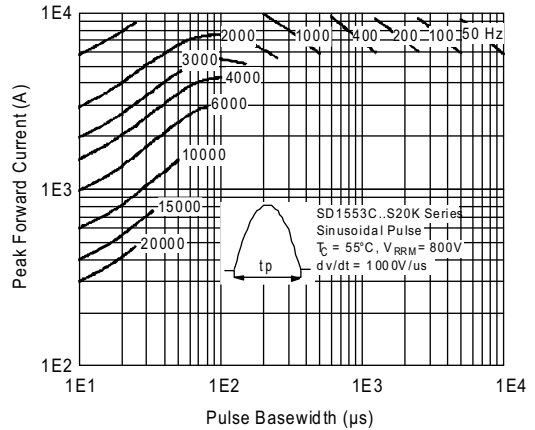


Fig. 29 - Frequency Characteristics

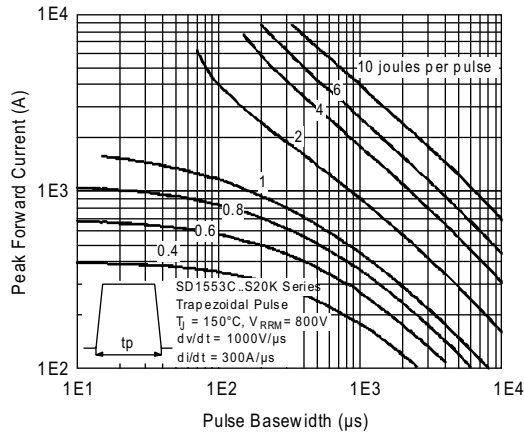


Fig. 30 - Maximum Total Energy Loss Per Pulse Characteristics

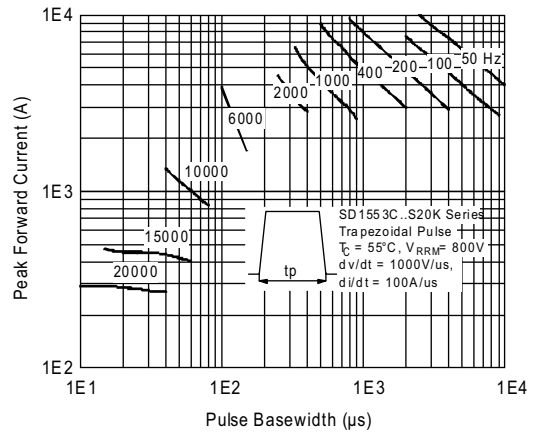


Fig. 33 - Frequency Characteristics

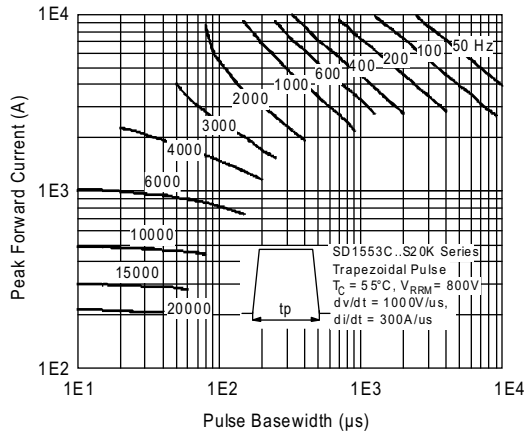


Fig. 31 - Frequency Characteristics

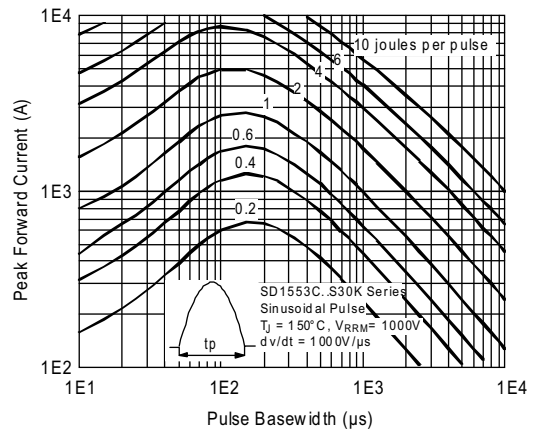


Fig. 34 - Maximum Total Energy Loss Per Pulse Characteristics

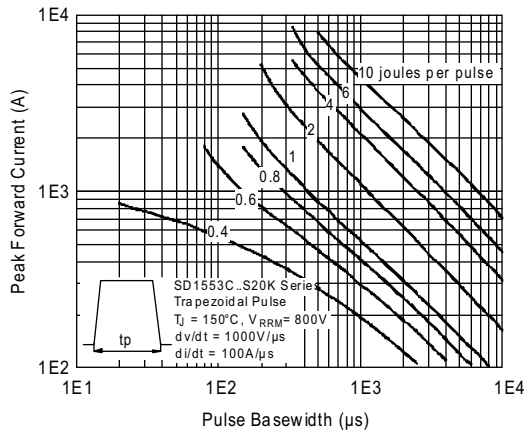


Fig. 32 - Maximum Total Energy Loss Per Pulse Characteristics

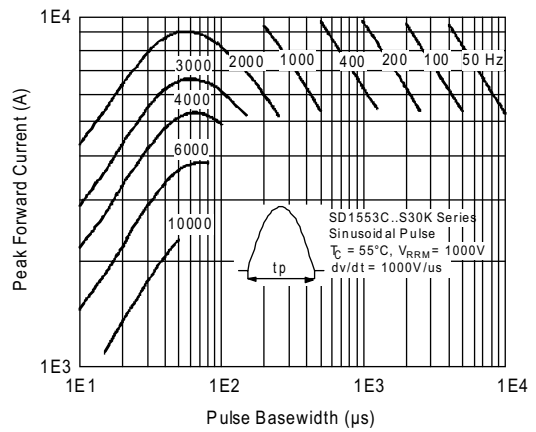


Fig. 35 - Frequency Characteristics

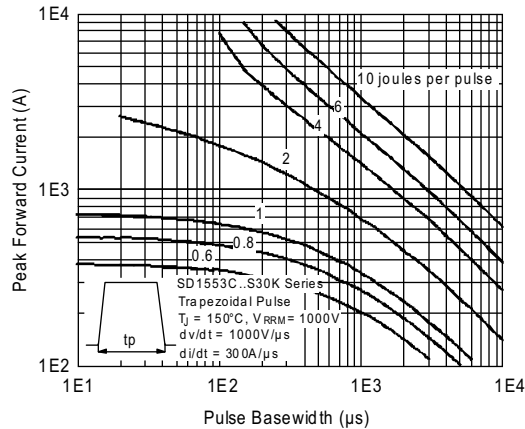


Fig. 36 - Maximum Total Energy Loss Per Pulse Characteristics

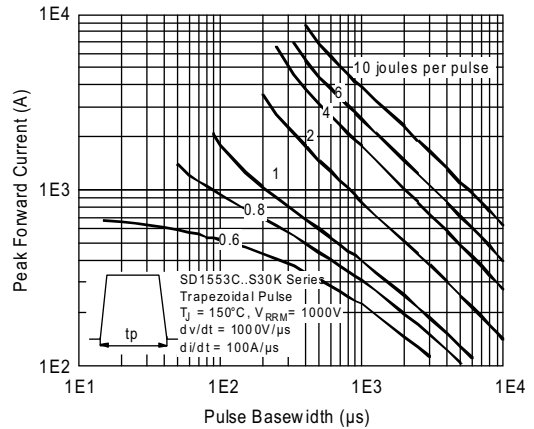


Fig. 38 - Maximum Total Energy Loss Per Pulse Characteristics

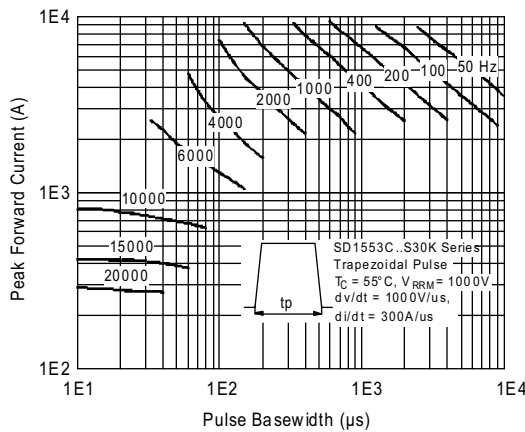


Fig. 37 - Frequency Characteristics

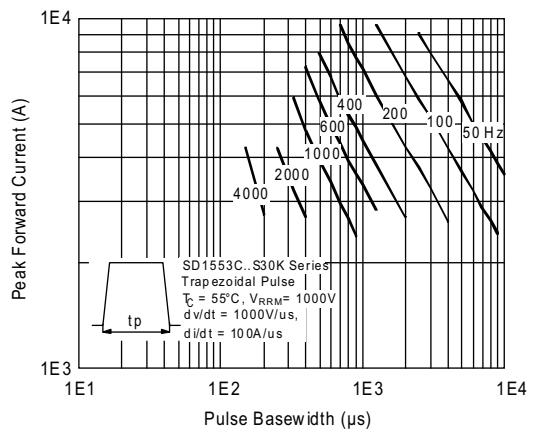


Fig. 39 - Frequency Characteristics

ORDERING INFORMATION TABLE

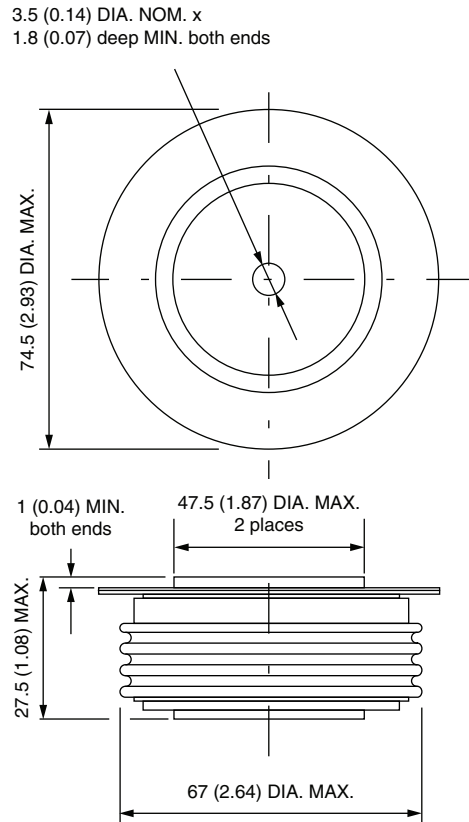
Device code	VS-	SD	155	3	C	30	S30	K
	①	②	③	④	⑤	⑥	⑦	⑧
	1	-	Vishay Semiconductors product	2	-	Diode	3	-
	3	-	Essential part number	4	-	3 = Fast recovery	5	-
	5	-	C = Ceramic PUK	6	-	Voltage code x 100 = VRRM (see Voltage Ratings table)	7	-
	7	-	t _{rr} code	8	-	K = PUK case DO-200AC (K-PUK)		

LINKS TO RELATED DOCUMENTS

Dimensions	www.vishay.com/doc?95247
------------	--

DO-200AC (K-PUK)

DIMENSIONS in millimeters (inches)



Quote between upper and lower pole pieces has to be considered after application of mounting force (see Thermal and Mechanical Specifications)



Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9